

FEATURES

- Secondary Side Synchronous Rectifier(SR) for Flyback converters
- Supports High-Side and Low-Side in DCM and Quasi-Resonant Topologies
- <300uA Low Quiescent Current
- Built-in HV Supplies without Aux-Winding for VDD supply
- Integrated with 45V Power MOSFET
- Built-in Protections:
 - VDD UVLO
 - VDD Clamper by >5mA sink current
- Available with SOP-8 Package

APPLICATIONS

- Flyback converters
- Chargers

GENERAL DESCRIPTION

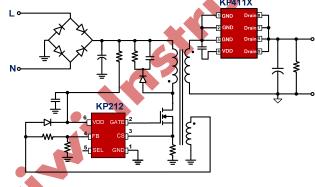
KP411X is a family of secondary side synchronous rectifier, that replaced Schottky diodes by combined with an ultra low on-state resistance power MOSFET for high-efficiency flyback converters. It supports High-Side and Low-Side in DCM and Quasi-Resonant Topologies.

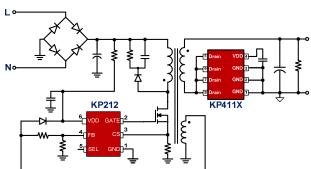
KP411X is built-in HV supplies for VDD capacitor, that can eliminate the aux-winding of VDD supply for cost saving.

KP411X integrates protections of Under Voltage Lockout (UVLO), VDD Clamper.

TYPICAL APPLICATION CIRCUIT









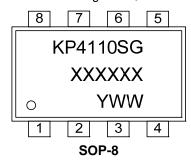
Pin Configuration



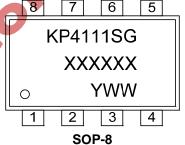
SOP-8

Marking Information

XXXXXX: Wafer Lot Code Y: Year, G for 2017 WW: Working Week, 01-52



XXXXXX: Wafer Lot Code Y: Year, G for 2017 WW: Working Week, 01-52



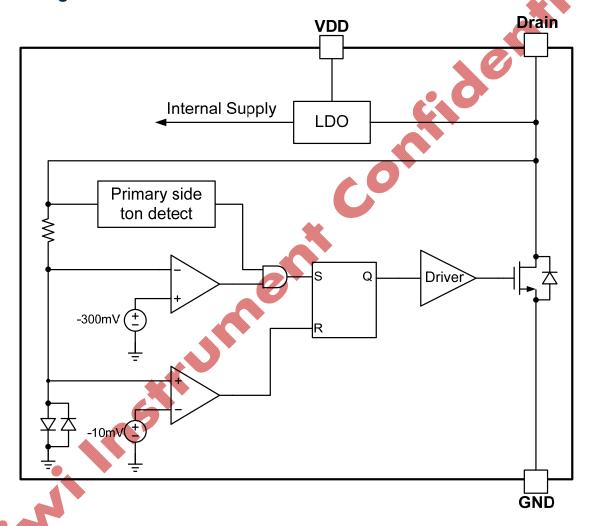
Pin Description

Pin Number	Pin Name	I/O	Description
1,2,3	GND	Р	IC Ground Pin and also the internal Power MOSFET Source Pin
4	VDD	Р	IC Power Supply Pin and 1uF Ceramic Capacitor is Recommended
5,6,7,8	Drain	I	Internal Power MOSFET Drain Pin

Ordering Information

Part Number	Description		
KP4110SGA	SOP-8, Halogen free in T&R, 4000Pcs/Reel		
KP4111SGA	SOP-8, Halogen free in T&R, 4000Pcs/Ree		

Block Diagram





Absolute Maximum Ratings (Note 1)

Parameter	Value	Unit	
Drain Pin Voltage Range	-0.3 to 45	٧	
VDD DC Supply Voltage	7.4	V	
VDD DC Clamp Current	5	mA	
Package Thermal ResistanceJunction to Ambient (SOP-8)	165	°C/W	
Maximum Junction Temperature	150	°C	
Storage Temperature Range	-65 to 150	°C	
Lead Temperature (Soldering, 10sec.)	260	°C	
ESD Capability, HBM (Human Body Model)	3	kV	
ESD Capability, MM (Machine Model)	250	V	

Recommended Operation Conditions (Note 2)

Parameter	Value	Unit
Operating Ambient Temperature	-40 to 125	°C

Electrical Characteristics (Ta = 25°C, if not otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Unit	
Supply Volta	Supply Voltage Section(VDD Pin)						
I _Q	Quiescent Operation Current	VDD=6V,Drain=0V	50	150	200	uA	
V _{DD_reg}	HV supply VDD regulation Voltage Drain=12V		6.7	7.1	7.5	V	
I _{HV}	HV supply current	Drain=12V,VDD=5.5V	15		30	mA	
V_{DD_ON}	VDD Start-up Voltage	VDD rising	3.7	4	4.3	V	
V_{DD_OFF}	VDD Under Voltage Lockout Enter	VDD falling	2.8	3.1	3.4	V	
V_{DD_Clamp}	VDD Zener Clamp Voltage	Clamp Voltage I(V _{DD}) = 5mA		7.4		V	



KP4110/KP4111

Secondary Side Synchronous Rectifier

Internal MOSFET and Control Section(Drain Pin)						
Vth_off	Internal synchronous MOSFET turn off threshold voltage		-15	-10	-5	mV
Vth_on	Itemnal synchronous MOSFET turn on threshold voltage			-300		mV
Pde on	Internal synchronous MOSFET	KP4110		15	20	mΩ
Rds_on	on-state resistance	KP4111		10	15	mΩ
Td_on	Internal synchronous MOSFET turn on delay time				200	ns
Td_off	Internal synchronous MOSFET turn off delay time		>		60	ns
V_{BR}	Internal synchronous MOSFET Drain Source Breakdown Voltage		45			V

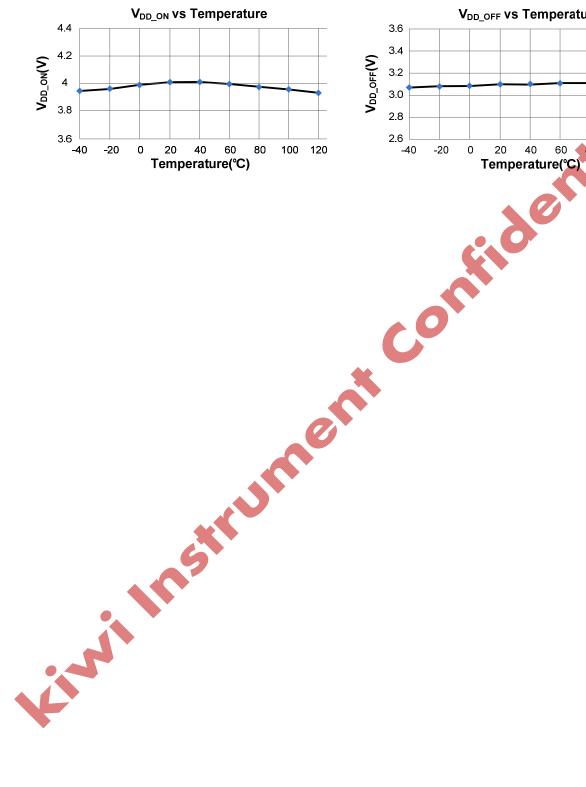
Note 1. Stresses listed as the above "Maximum Ratings" may cause permanent damage to the device. These are for stress ratings. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to maximum rating conditions for extended periods may remain possibility to affect device reliability.

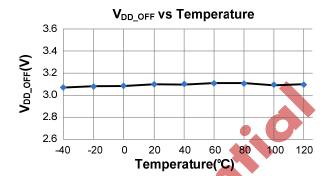
, (side i) Note 2. The device is not guaranteed to function outside its operating conditions.





Characterization Plots







Operation Description

KP411X is a family of secondary side synchronous rectifier, that replaced Schottky diodes by combined with an ultra low on-state resistance power MOSFET for high-efficiency flyback converters. It supports High-Side and Low-Side in DCM and Quasi-Resonant Topologies. KP411X is built-in HV supplies for VDD capacitor, that can eliminate the aux-winding of VDD supply for cost saving

7.1V Regulator

In KP411X, the 7.1V regulator charges VDD holdup capacitor to 7.1V by drawing a current from the Drain pin during the on state of primary side. A capacitor value about 1uF is sufficient for both high frequency decoupling and energy storage.

System Start-Up Operation

After system power up, VDD hold up capacitor is charged by the internal LDO through Drain pin.

When VDD pin voltage is below UVLO threshold (3.1V typically), the IC is in sleep mode and the internal synchronous MOSFET is keeping off. The current flows through body diode of the internal synchronous MOSFET. When VDD pin voltage reaches the turn on threshold (4V typically), the IC begins working. The internal synchronous MOSFET can be only turned on during the demagnetization time of the transformer.

Turn-on Phase

When the internal synchronous MOSFET is off, current will flow through its body diode which can generate a negative Vds(<-500mV) across it. The body diode drop voltage Vds is much smaller than

the turn on threshold of KP411X (-300mV typically), which will turn on the internal synchronous MOSFET after about 200ns turn on delay (Td on). (Shown in Fig 1)

• Turn-off Phase

During the turn-on period of the internal synchronous MOSFET, The KP411X senses the drop voltage Vds across the on-state resistance of the MOSFET. When Vds is higher than the turn off threshold (-10mV typically), the internal synchronous MOSFET will be turned off after about 60ns turn on delay (Td_off). (Shown in Fig 1)

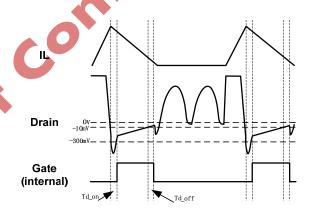


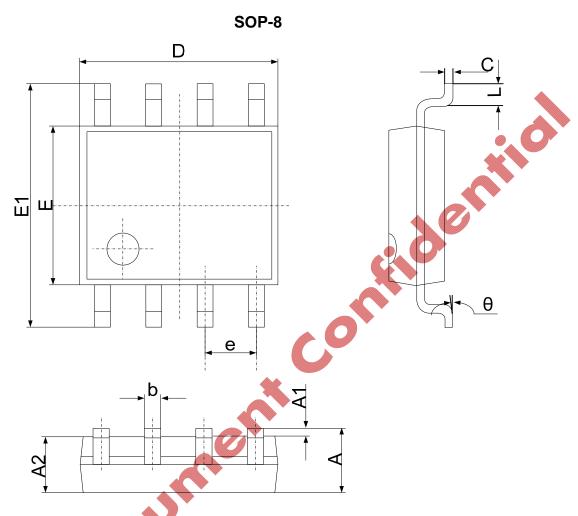
Fig 1

Leading Edge Blanking (LEB)

Each time the internal synchronous MOSFET is switched on, a turn-on spike occurs across the Drain and GND. To avoid premature termination of the switching pulse, an internal leading edge blanking circuit is built in. During this blanking period (1us typically), the turn-off comparator is disabled and cannot switch off the internal synchronous MOSFET.



Package Dimension



Symbol	Dimensions in Millimeters		Dimensions in Inches		
	Min	Max	Min	Max	
А	1.350	1.750	0.053	0.069	
A1 🔺	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
C	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



Revision History

REV.	DESCRIPTION		
1.0	First Release		
1.01	Modify "Absolute Maximum Ratings" and	"Electrical Characteristics" table	
	7		
12	Hangzhou (R&D Center):	Shenzhen (Marketing/Field Support):	
	1.0	1.01 Modify "Absolute Maximum Ratings" and Hangzhou	

Contact Us:

Add: 2060 Walsh Ave, Suite 244,

Santa Clara, CA, 95050 Tel: 1-408-475-6888 Fax: 1-408-905-6912

E-mail: marketing@kiwiinst.com

Add: Room 1201, Building C, No.581 HuoJu Rd., Binjiang Dist., Hangzhou,

P.R.C

Tel: (86) 571-8795-8612 Fax: (86) 571-8795-5363

E-mail: marketing@kiwiinst.com.cn

Add: B302-B303, University Creative Park, Xili Rd., Nanshan

Dist., Shenzhen, P.R.C Tel: (86)755-8204-2689 Fax: (86)755-8204-2192

E-mail: marketing@kiwiinst.com.cn

Disclaimer

Information that is provided by Kiwi Instrument Corporation is believed to be accurate and reliable. Kiwi instrument reserves the right to make any change in circuit design, specification or other related things if necessary without notice at any time. No third party intellectual property infringement of the applications should be guaranteed by users when integrating Kiwi instrument products into any application. No legal responsibility for any said applications is assumed by Kiwi Instrument.